Descriptions

This ±30V N-Channel and P-Channel compleme-ntary Enhancement MOSFET in a SOP-8 Plastic Package.

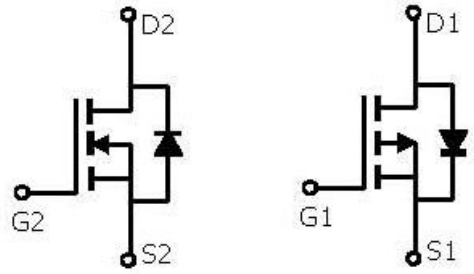
Features

N-channel	P-channel
V_{DS}(V)=30V	Vos(V)=-30V
I_D=6.9A	Ib=-6A
$R_{DS(ON)}$<32mΩ(V_{GS}=10V)	Ros(ON)<65mΩ(VGs=-10V)
$R_{DS(ON)}$<36mΩ(V_{GS}=4.5V)	Ros(ON)<75mΩ(Vgs=-4.5V)
Halogen-free Product.	

Applications

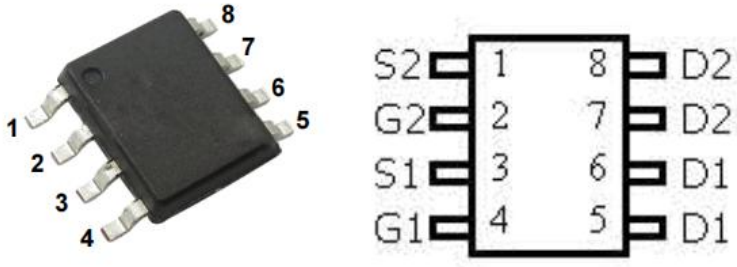
These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies. And suitable for use as a load switch or in PWM applications.

Equivalent Circuit



n-channel p-channel

Pinning



Absolute Maximum Ratings(Ta=25℃)

Parameter	Symbol	Rating		Unit
		N-channel	P-channel	
Drain-Source Voltage	V_{DSS}	±30		V
Gate-Source Voltage	V_{GSS}	±12		V
Continuous Drain Current [A]	I_D (T_A=25℃)	6.9	-6.0	A
	I_D (T_A=70℃)	5.8	-5.0	A
Pulsed Drain Current [B]	I_{DM}	±30		A
Power Dissipation	P_D (T_A=25℃)	2		W
	P_D (T_A=70℃)	1.44		W
Maximum Junction-to-Ambient [A]	$R_{\theta JA}$(t≤10s)	62.5		℃/W
	$R_{\theta JA}$	110		℃/W
Maximum Junction-to-Lead [C]	$R_{\theta JL}$	60	4	℃/W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to +150		℃

Notes:

A:The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C.The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

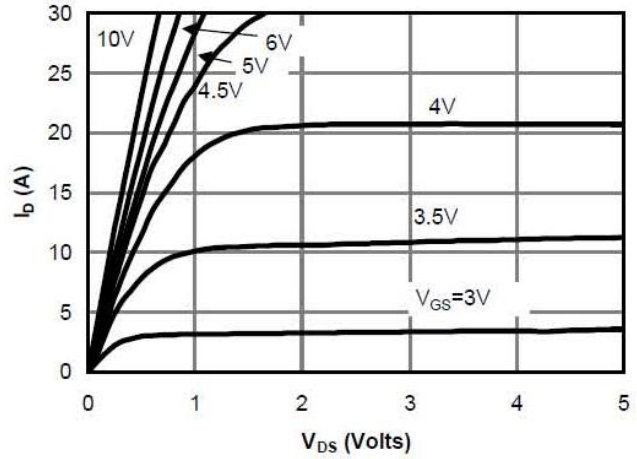
D.The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

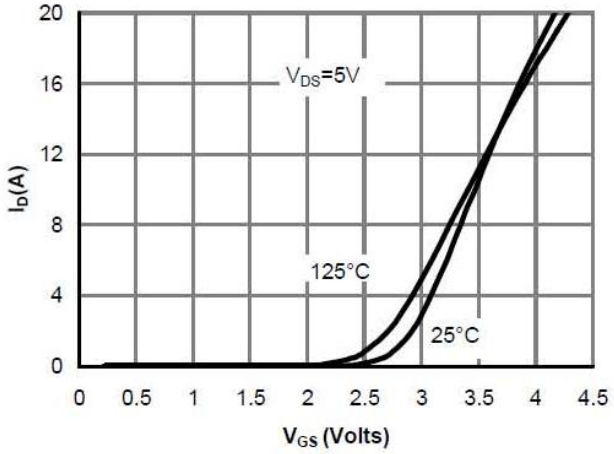
E.These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

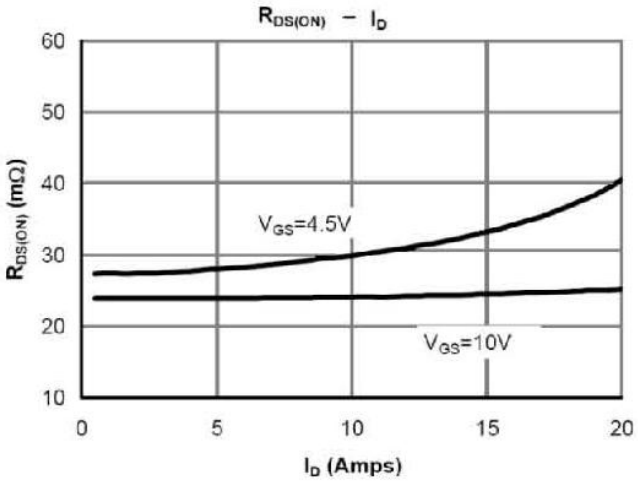
Electrical Characteristics(Ta=25℃)

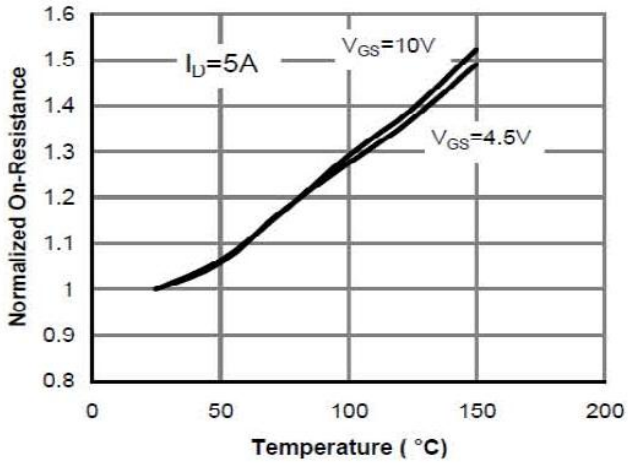
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=24V V_{GS}=0V			1.0	μA
		V_{DS}=24V V_{GS}=0V T_J=55℃			5.0	μA
Gate-Body leakage current	I_{GSS}	V_{GS}=±12V V_{DS}=0V			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250μA	0.65		1.3	V
On state drain current	$I_{D(on)}$	V_{DS}=4.5V $_{GS}$=5.0V	6.9			A
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V I_D=6.9A		24	32	mΩ
		V_{GS}=10V I_D=6.9A T_J=125℃		32.3	38	mΩ
		V_{GS}=4.5V I_D=5.0A		27	36	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5.0V I_D=5.0A		9		S
Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=1.0A		0.76	1.0	V
Input Capacitance	C_{iss}	V_{DS}=15V V_{GS}=0V f=1.0MHz		680		pF
Output Capacitance	C_{oss}			102		pF
Reverse Transfer Capacitance	C_{rss}			77		pF
Gate resistance	R_g	V_{DS}=0V V_{GS}=0V f=1.0MHz		3.0		Ω
Total Gate Charge(10V)	Q_g	V_{GS}=10V V_{DS}=15V I_D=6.9A		13.84		nC
Total Gate Charge(4.5V)				6.74		nC
Gate-Source Charge	Q_{gs}			1.82		nC
Gate-Drain Charge	Q_{gd}			3.2		nC
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=15V V_{GS}=10V R_L=2.1Ω R_{GEN}=3Ω		4.6		ns
Turn-On Rise Time	t_r			4.1		ns
Turn-Off Delay Time	$t_{d(off)}$			20.6		ns
Turn-Off Fall Time	t_f			5.2		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F=6.9A dI/dt=100A/μs		16.5		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F=6.9A dI/dt=100A/μs		7.8		nC

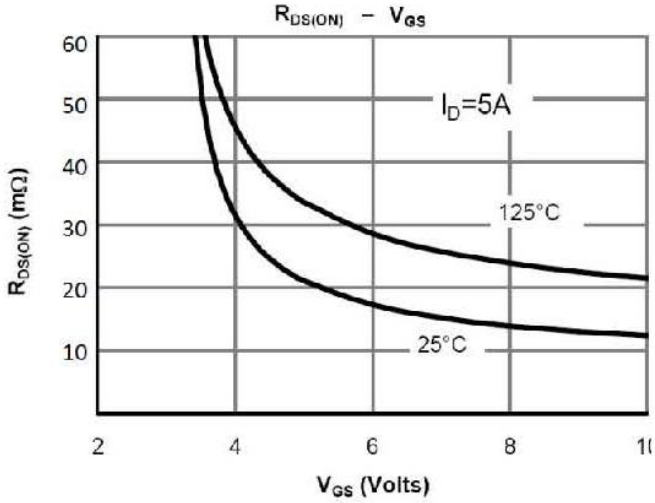
Electrical Characteristic Curve

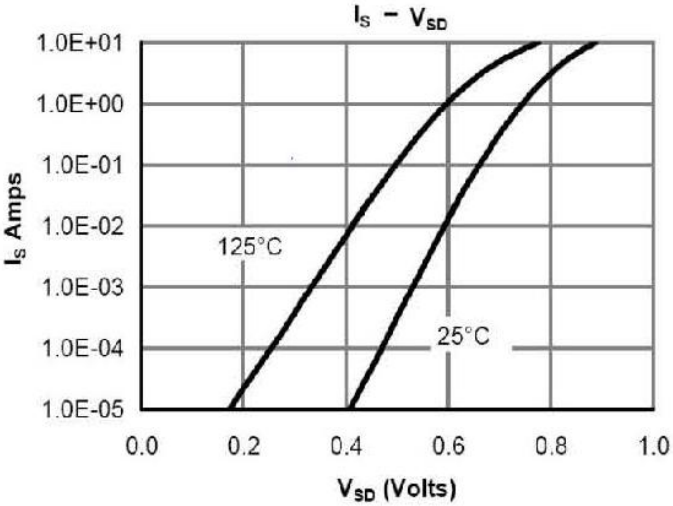




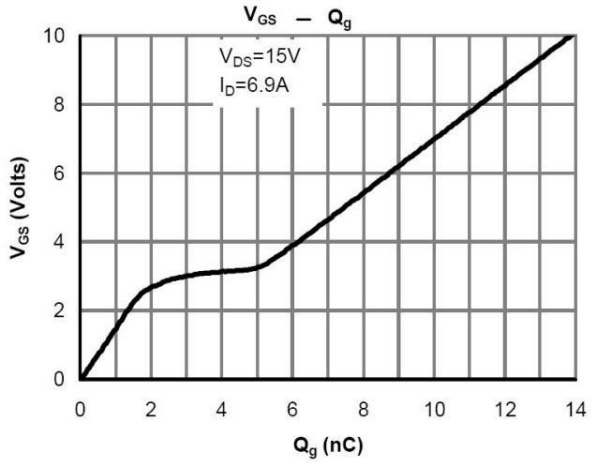


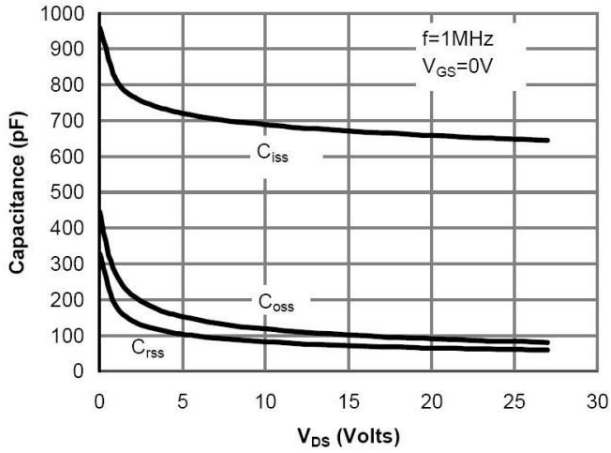


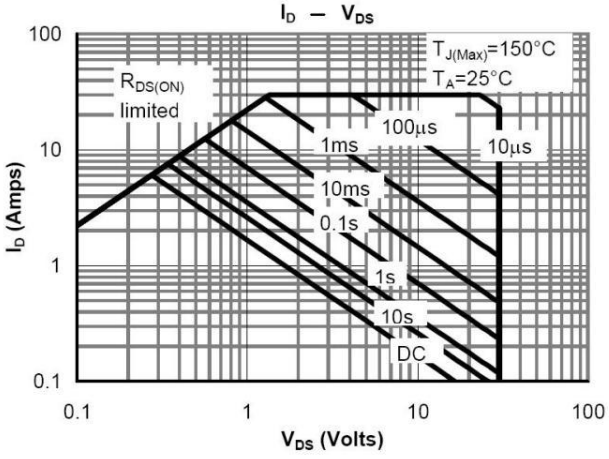


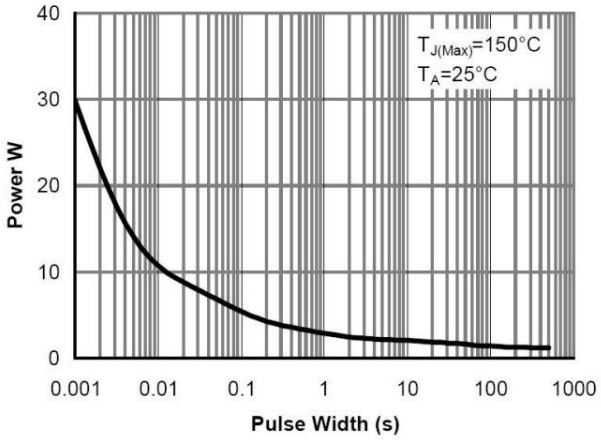


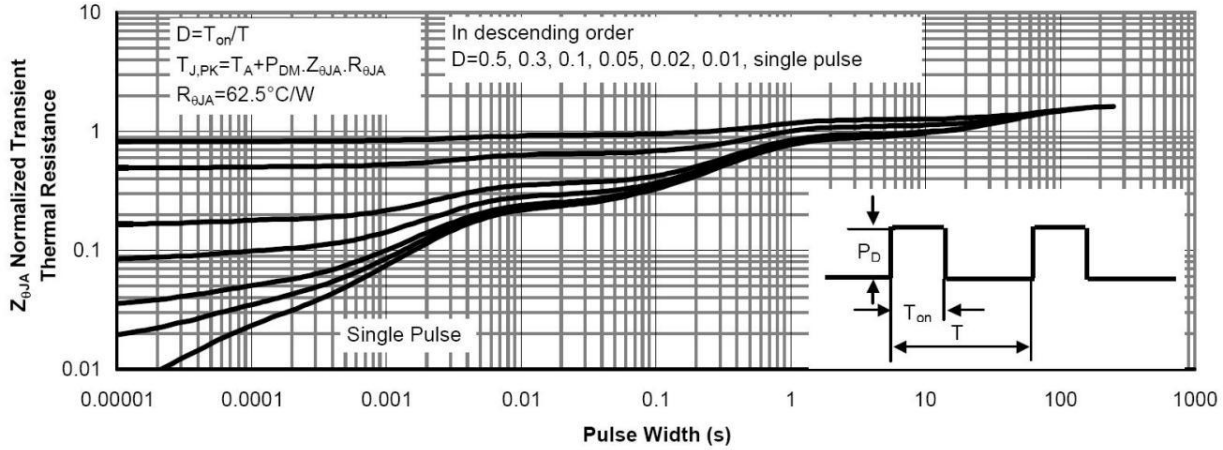
Electrical Characteristic Curve



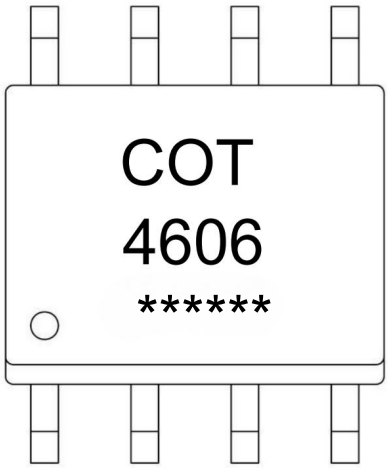








Marking Instructions



Note:

COT: Company Logo

4606: Product Type.

******: Lot No. Code, code change with Lot No.

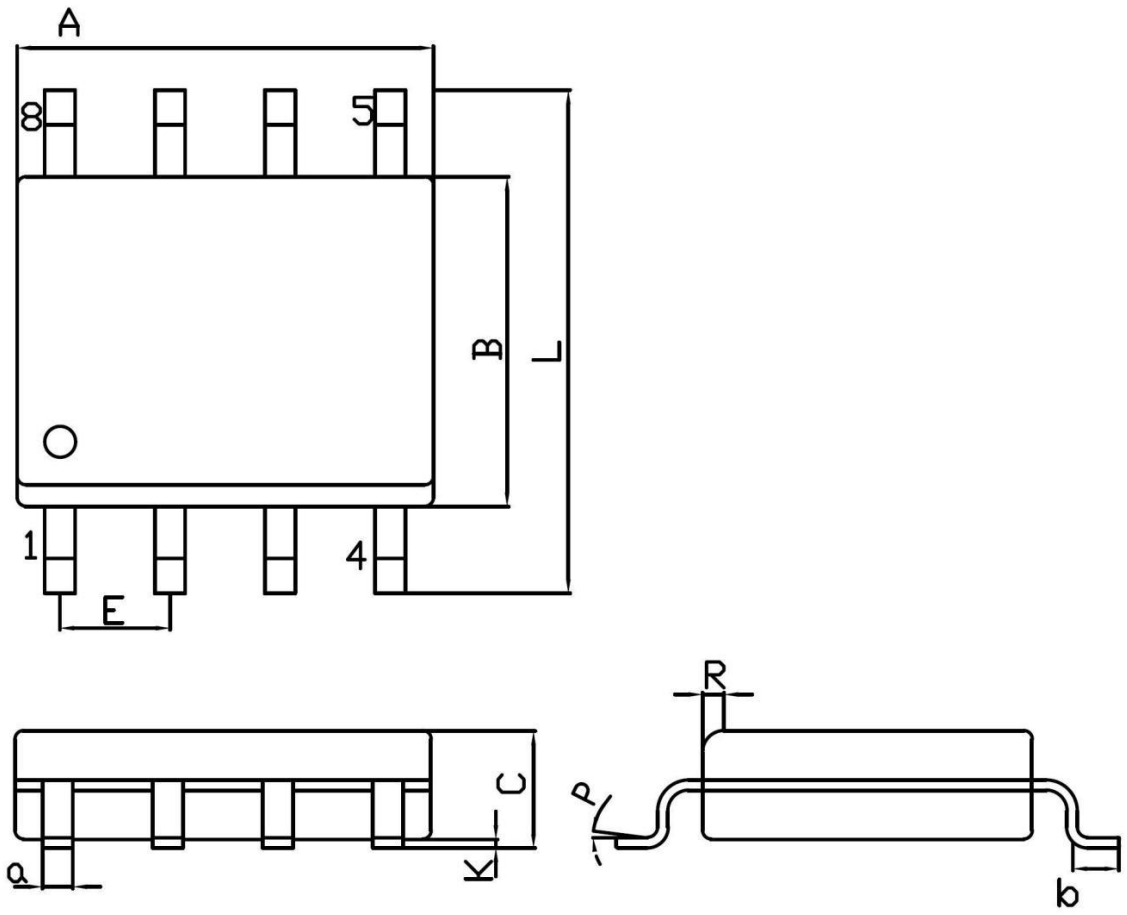
Packaging SPEC

REEL INFORMATION

Package Type	Units					Dimension (unit：mm³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOP-8	4,000	2	8,000	6	48,000	13″ ×12	360×360×50	380×335×366

Package Outline Dimensions

SOP-8 Unit:mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.70	5.10	C	1.35	1.75
B	3.70	4.10	a	0.35	0.49
L	5.80	6.20	R	0.30	0.60
E	1.27BSC		P	0°	7°
K	0.12	0.22	b	0.40	1.25